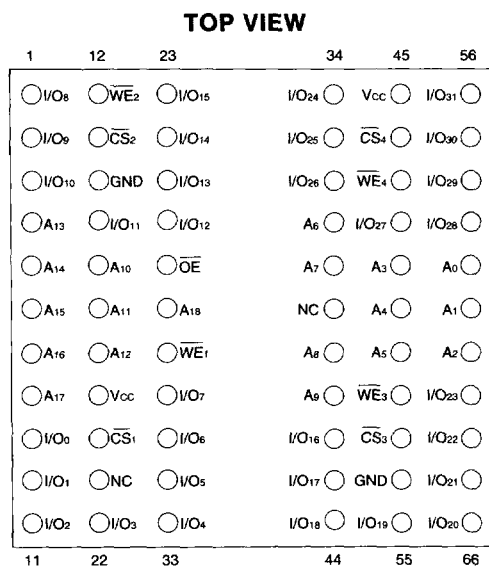


**512Kx32 SRAM MODULE** PRELIMINARY***FEATURES**

- Access Times of 70, 85, 100, 120nS
- Packaging
 - 66-pin, PGA Type, 1.385 inch square, Hermetic Ceramic HIP (Package 402), SMD Number 5962-94611
 - 68 lead, 40mm Hermetic Low Capacitance CQFP, 5.1mm (0.200") (Package 501) SMD Number 5962-95624
 - 68 lead, 40mm Hermetic Low Profile CQFP, 3.5mm (0.140"), (Package 502)
 - 68 lead, Hermetic CQFP (G2), 22mm (0.880 inch) square (Package 500). Designed to fit JEDEC 68 lead 0.990" CQFJ footprint (Fig. 3)
- Organized as 512Kx32, User Configurable as 1024Kx16 or 2Mx8
- Commercial, Industrial and Military Temperature Ranges
- TTL Compatible Inputs and Outputs
- 5 Volt Power Supply
- Low Power CMOS
- Built in Decoupling Caps and Multiple Ground Pins for Low Noise Operation
- Weight
 - WS512K32-XG2X- 8 grams typical
 - WS512K32-XH2X - 13 grams typical
 - WS512K32-XG4X - 20 grams typical

* This data sheet describes a product under development, not fully characterized, and is subject to change without notice.

FIG. 1 PIN CONFIGURATION FOR WS512K32N-XH2X, SMD 5962-94611**PIN DESCRIPTION**

I/O0-31	Data Inputs/Outputs
A0-18	Address Inputs
WE1-4	Write Enables
CS1-4	Chip Selects
OE	Output Enable
Vcc	Power Supply
GND	Ground
NC	Not Connected

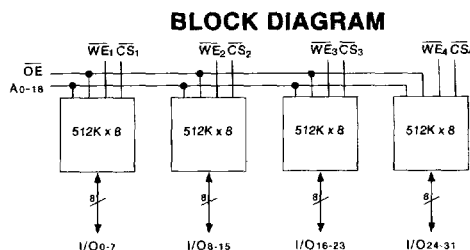
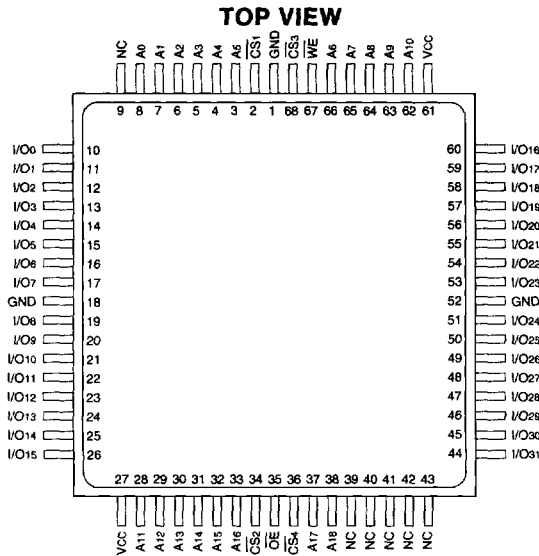


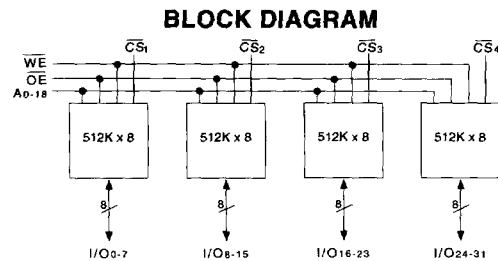


FIG. 2 PIN CONFIGURATION FOR WS512K32F-XG4X Low Capacitance, SMD 5962-95624 AND WS512K32-XG4TX Low Profile, SMD 5962-94611



PIN DESCRIPTION

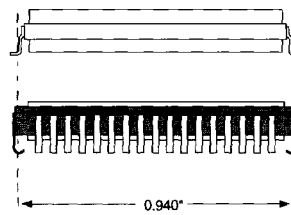
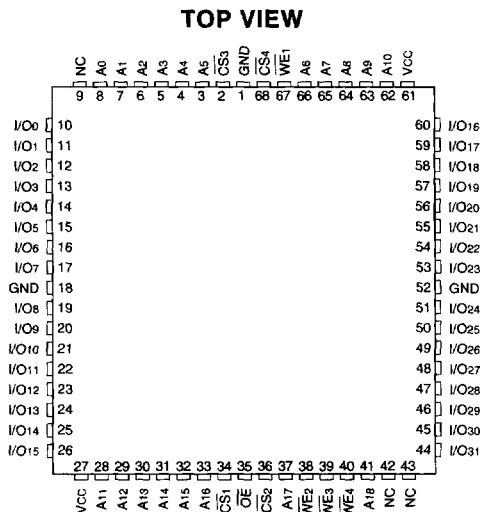
I/O0-31	Data Inputs/Outputs
A0-18	Address Inputs
WE	Write Enable
CS1-4	Chip Selects
OE	Output Enable
Vcc	Power Supply
GND	Ground
NC	Not Connected



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SRAM MODULES

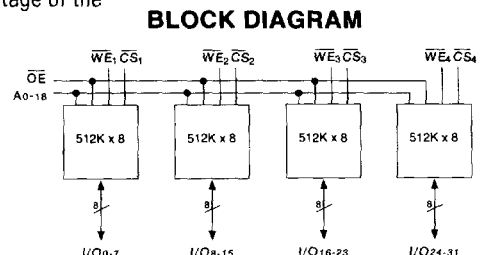
FIG. 3 PIN CONFIGURATION FOR WS512K32-XG2X, SMD 5962-94611



The White 68 lead G2 CQFP fills the same fit and function as the JEDEC 68 lead CQFJ or 68 PLCC. But the G2 has the TCE and lead inspection advantage of the CQFP form.

PIN DESCRIPTION

I/O0-31	Data Inputs/Outputs
A0-18	Address Inputs
WE1-4	Write Enables
CS1-4	Chip Selects
OE	Output Enable
Vcc	Power Supply
GND	Ground
NC	Not Connected





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	V _{CC} +0.5	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	7.0	V

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.5	+0.8	V
Operating Temp (Mil)	T _A	-55	+125	°C

TRUTH TABLE

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	H	H	Out Disable	High Z	Active
L	X	L	Write	Data In	Active

CAPACITANCE

(T_A = +25°C)

Parameter	Symbol	Conditions	Max	Unit
$\overline{OE}$ capacitance	C _{OE}	V _{IN} = 0 V, f = 1.0 MHz	50	pF
$\overline{WE}$ 1-4 capacitance HIP (PGA)	C _{WE}	V _{IN} = 0 V, f = 1.0 MHz	20	pF
CQFP G4			50	
CQFP G2			20	
$\overline{CS}$ 1-4 capacitance	C _{CS}	V _{IN} = 0 V, f = 1.0 MHz	20	pF
Data I/O capacitance	C _{I/O}	V _{I/O} = 0 V, f = 1.0 MHz	20	pF
Address input capacitance	C _{AD}	V _{IN} = 0 V, f = 1.0 MHz	50	pF

This parameter is guaranteed by design but not tested.

LOW CAPACITANCE CQFP

(T_A = +25°C)

Parameter	Symbol	Conditions	Max	Unit
$\overline{OE}$ capacitance	C _{OE}	V _{IN} = 0 V, f = 1.0 MHz	32	pF
CQFP G4 capacitance	C _{WE}	V _{IN} = 0 V, f = 1.0 MHz	32	pF
$\overline{CS}$ 1-4 capacitance	C _{CS}	V _{IN} = 0 V, f = 1.0 MHz	15	pF
Data I/O capacitance	C _{I/O}	V _{I/O} = 0 V, f = 1.0 MHz	15	pF
Address input capacitance	C _{AD}	V _{IN} = 0 V, f = 1.0 MHz	32	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	Conditions			Units
			Min	Max	
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	$\overline{CS} = V_{IH}, \overline{OE} = V_{IH}, V_{OUT} = \text{GND to } V_{CC}$		10	μA
Operating Supply Current x 32 Mode	I _{CC} x 32	$\overline{CS} = V_{IL}, \overline{OE} = V_{IH}, f = 5\text{MHz}, V_{CC} = 5.5$		200	mA
Standby Current	I _{SB}	$\overline{CS} = V_{IH}, \overline{OE} = V_{IH}, f = 5\text{MHz}, V_{CC} = 5.5$		4.0	mA
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA, V _{CC} = 4.5		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -1.0mA, V _{CC} = 4.5	2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V

DATA RETENTION CHARACTERISTICS

(T_A = -55°C to +125°C)

Parameter	Symbol	Conditions				Units
			Min	Typ	Max	
Data Retention Supply Voltage	V _{DR}	$\overline{CS}$ V _{CC} - 0.2V	2.0		5.5	V
Data Retention Current	I _{CCDR1}	V _{CC} = 3V		0.4	1.6	mA



AC CHARACTERISTICS

(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter Read Cycle	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	70		85		100		120		nS
Address Access Time	t _{AA}		70		85		100		120	nS
Output Hold from Address Change	t _{OH}	5		5		5		5		nS
Chip Select Access Time	t _{ACS}		70		85		100		120	nS
Output Enable to Output Valid	t _{OE}		35		40		50		60	nS
Chip Select to Output in Low Z	t _{CLZ'}	10		10		10		10		nS
Output Enable to Output in Low Z	t _{OLZ'}	5		5		5		5		nS
Chip Disable to Output in High Z	t _{CHZ'}		25		25		35		35	nS
Output Disable to Output in High Z	t _{OHZ'}		25		25		35		35	nS

1. This parameter is guaranteed by design but not tested.

AC CHARACTERISTICS

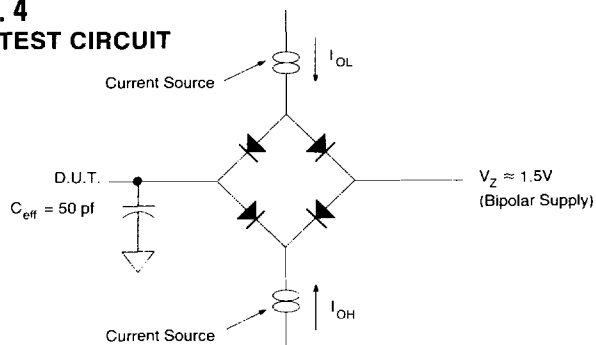
(V_{CC} = 5.0V, V_{SS} = 0V, T_A = -55°C to +125°C)

Parameter Write Cycle	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	70		85		100		120		nS
Chip Select to End of Write	t _{cw}	60		75		80		100		nS
Address Valid to End of Write	t _{AW}	60		75		80		100		nS
Data Valid to End of Write	t _{DW}	30		30		40		40		nS
Write Pulse Width	t _{WP}	50		50		60		60		nS
Address Setup Time	t _{AS}	0		0		0		0		nS
Address Hold Time	t _{AH}	5		5		5		5		nS
Output Active from End of Write	t _{OW'}	5		5		5		5		nS
Write Enable to Output in High Z	t _{WHZ'}		25		25		35		35	nS
Data Hold from Write Time	t _{DH}	0		0		0		0		nS

1. This parameter is guaranteed by design but not tested.

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SRAM MODULES

FIG. 4
AC TEST CIRCUIT

AC TEST CONDITIONS

Parameter	Typ	Unit
Input Pulse Levels	V _{IL} = 0, V _{IH} = 3.0	V
Input Rise and Fall	5	nS
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:

V_Z is programmable from -2V to +7V
I_{OL} & I_{OIH} programmable from 0 to 16mA
Tester Impedance Z₀ = 75
V_Z is typically the midpoint of V_{IH} and V_{OL}.
I_{OL} & I_{OIH} are adjusted to simulate a typical resistive load circuit.
ATE tester includes jig capacitance



FIG. 5
TIMING WAVEFORM - READ CYCLE

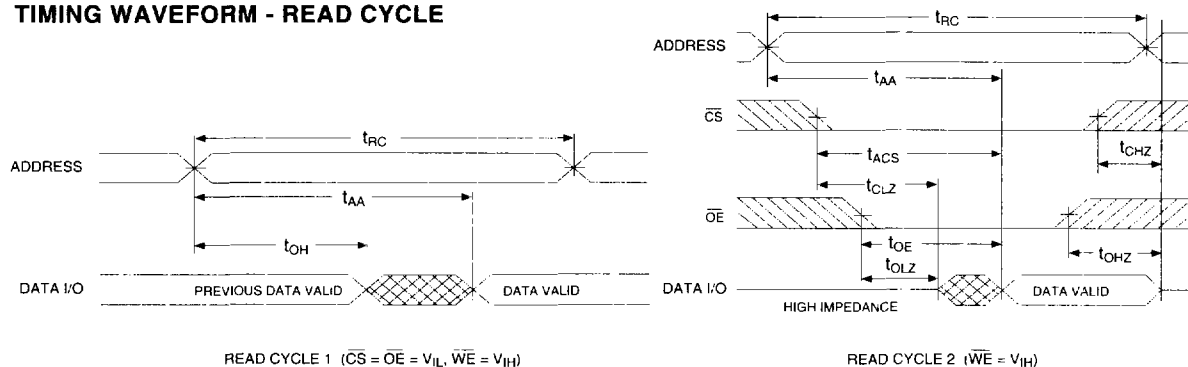


FIG. 6
WRITE CYCLE - $\overline{WE}$ CONTROLLED

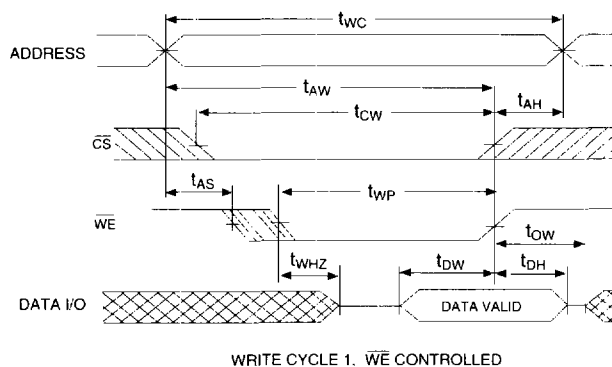
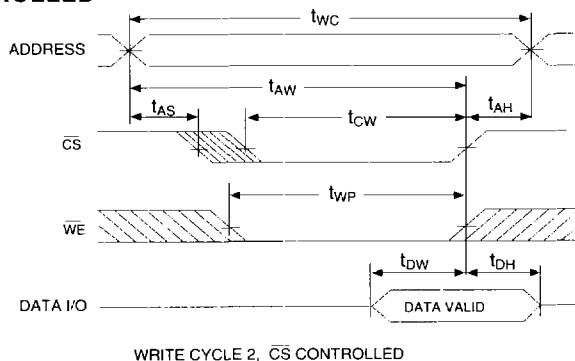


FIG. 7
WRITE CYCLE - $\overline{CS}$ CONTROLLED



**ORDERING INFORMATION****W S 512K 32 X - XXX X X****DEVICE GRADE:**

Q = MIL-STD-883 Compliant
M = Military Screened -55°C to +125°C
I = Industrial -40°C to 85°C
C = Commercial 0°C to +70°C

PACKAGE TYPE:

H2 = Ceramic Hex-In-line Package, HIP (Package 402)
G2 = 22mm Ceramic Quad Flat Pack, CQFP (Package 500)
G4 = 40mm Ceramic Quad Flat Pack, CQFP (Package 501)
for Low Capacitance version
G4T = 40mm Low Profile CQFP (Package 502)

ACCESS TIME IN nS**IMPROVEMENT MARK:**

N = No Connect at pin 21 and 39 in HIP for Upgrades
F = Low Capacitance CQFP

ORGANIZATION, 512Kx32

User configurable as 1Mx16 or 2Mx8

SRAM**WHITE MICROELECTRONICS**



DEVICE TYPE	SPEED	PACKAGE	SMD NO.
512K x 32 SRAM Module	120nS	66 pin HIP (H2)	5962-94611 01HXX
512K x 32 SRAM Module	100nS	66 pin HIP (H2)	5962-94611 02HXX
512K x 32 SRAM Module	85nS	66 pin HIP (H2)	5962-94611 03HXX
512K x 32 SRAM Module	70nS	66 pin HIP (H2)	5962-94611 04HXX
512K x 32 SRAM Module	120nS	68 pin CQFP Low Profile (G4T)	5962-94611 01HZX
512K x 32 SRAM Module	100nS	68 pin CQFP Low Profile (G4T)	5962-94611 02HZX
512K x 32 SRAM Module	85nS	68 pin CQFP Low Profile (G4T)	5962-94611 03HZX
512K x 32 SRAM Module	70nS	68 pin CQFP Low Profile (G4T)	5962-94611 04HZX
512K x 32 SRAM Module	120nS	68 pin CQFP/J (G2)	5962-94611 01HMX
512K x 32 SRAM Module	100nS	68 pin CQFP/J (G2)	5962-94611 02HMX
512K x 32 SRAM Module	85nS	68 pin CQFP/J (G2)	5962-94611 03HMX
512K x 32 SRAM Module	70nS	68 pin CQFP/J (G2)	5962-94611 04HMX
512K x 32 SRAM Module	120nS	68 pin CQFP Low Capacitance	5962-95624 01HNX
512K x 32 SRAM Module	100nS	68 pin CQFP Low Capacitance	5962-95624 02HNX
512K x 32 SRAM Module	85nS	68 pin CQFP Low Capacitance	5962-95624 03HNX
512K x 32 SRAM Module	70nS	68 pin CQFP Low Capacitance	5962-95624 04HNX